



## Stud Diode

$V_{RSM}$	$V_{RRM}$	$I_{FRMS} = 500 \text{ A}$ (maximum value for continuous operation)		
$V$	$V$	$I_{FAV} = 240 \text{ A}$ (sin. 180; $T_c = 125^\circ\text{C}$ )		
400	400	SKN 240/04	SKR 240/04	
800	800	SKN 240/08	SKR 240/08	
1200	1200	SKN 240/12	SKR 240/12	
1400	1400	SKN 240/14	SKR 240/14	
1600	1600	SKN 240/16	SKR 240/16	
1800	1800	SKN 240/18	SKR 240/18	

## Rectifier Diode

### SKN 240

### SKR 240

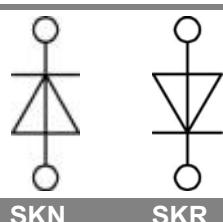
Symbol	Conditions	Values	Units
$I_{FAV}$	sin. 180; $T_c = 100^\circ\text{C}$	320	A
$I_D$	$K = 0,55$ ; $T_a = 45^\circ\text{C}$ ; B2 / B6	340 / 480	A
	$K = 0,55F$ ; $T_a = 35^\circ\text{C}$ ; B2 / B6	620 / 840	A
$I_{FSM}$	$T_{vj} = 25^\circ\text{C}$ ; 10 ms $T_{vj} = 180^\circ\text{C}$ ; 10 ms	6000	A
$i^2t$	$T_{vj} = 25^\circ\text{C}$ ; 8,3 ... 10 ms $T_{vj} = 180^\circ\text{C}$ ; 8,3 ... 10 ms	5000 180000 125000	A <sup>2</sup> s
$V_F$	$T_{vj} = 25^\circ\text{C}$ ; $I_F = 750 \text{ A}$	max. 1,4	V
$V_{(TO)}$	$T_{vj} = 180^\circ\text{C}$	max. 0,85	V
$r_T$	$T_{vj} = 180^\circ\text{C}$	max. 0,6	mΩ
$I_{RD}$	$T_{vj} = 180^\circ\text{C}$ ; $V_{RD} = V_{RRM}$	max. 60	mA
$Q_{rr}$	$T_{vj} = 160^\circ\text{C}$ ; $-di_F/dt = 10 \text{ A}/\mu\text{s}$	200	μC
$R_{th(j-c)}$		0,2	K/W
$R_{th(c-s)}$		0,03	K/W
$T_{vj}$		- 40 ... + 180	°C
$T_{stg}$		- 55 ... + 180	°C
$V_{isol}$		-	V~
$M_s$	to heatsink	30	Nm
$a$		5 * 9,81	m/s <sup>2</sup>
$m$	approx.	250	g
Case		E 15	

## Features

- Reverse voltages up to 1800 V
- Hermetic metal case with glass insulator
- Threaded stud ISO M16 x 1,5
- SKN / SKR 240/04 ... /16 also available with threaded stud 3/4 - 16 UNF (e.g. SKR 240/12 UNF)
- SKN: anode to stud, SKR: cathode to stud

## Typical Applications

- All-purpose mean power rectifier diodes
- Cooling via heatsinks
- Non-controllable and half-controllable rectifiers
- Free-wheeling diodes
- Recommended snubber network:  
 $RC: 0,5 \mu\text{F}, 30 \Omega$  ( $P_R = 2\text{W}$ ),  
 $R_P = 50 \text{k}\Omega$  ( $P_R = 20 \text{W}$ )



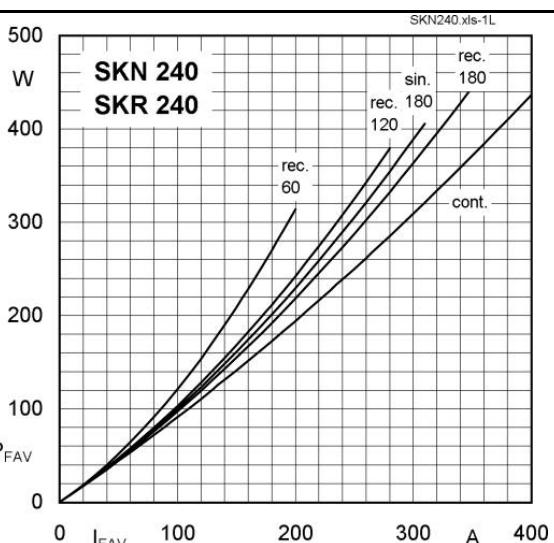


Fig. 1L Power dissipation vs. forward current

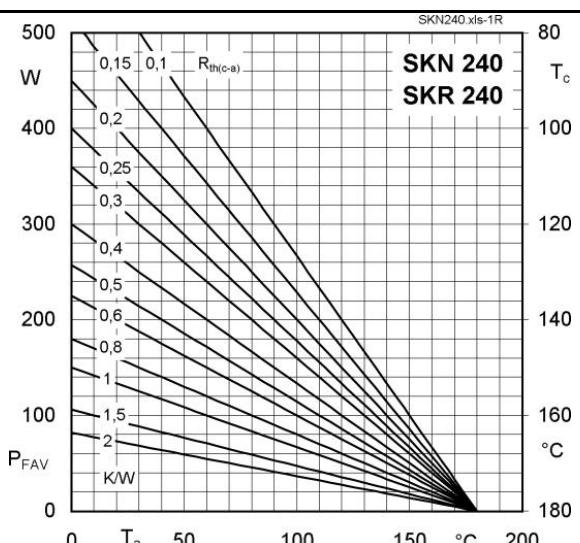


Fig. 1R Power dissipation vs. ambient temperature

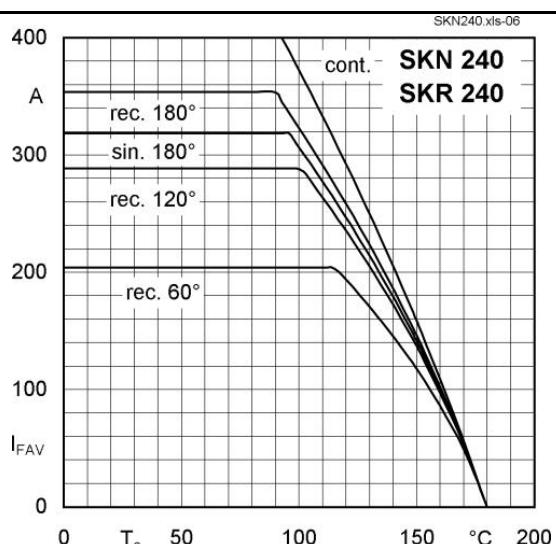


Fig. 2 Forward current vs. case temperature

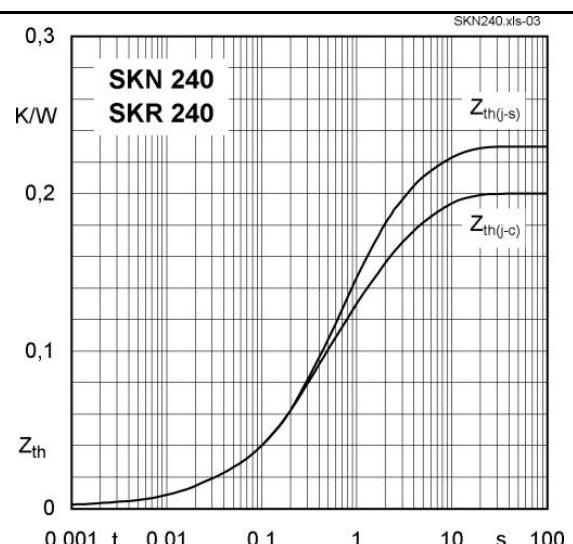


Fig. 4 Transient thermal impedance vs. time

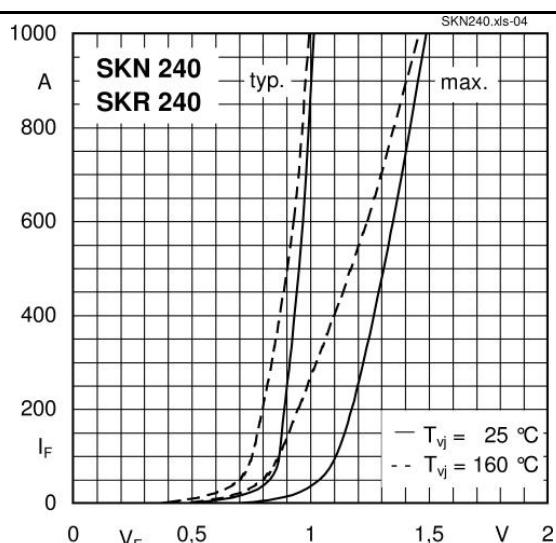


Fig. 5 Forward characteristics

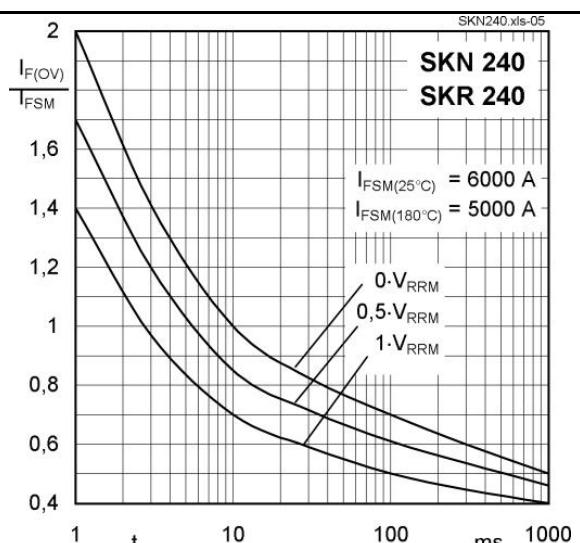
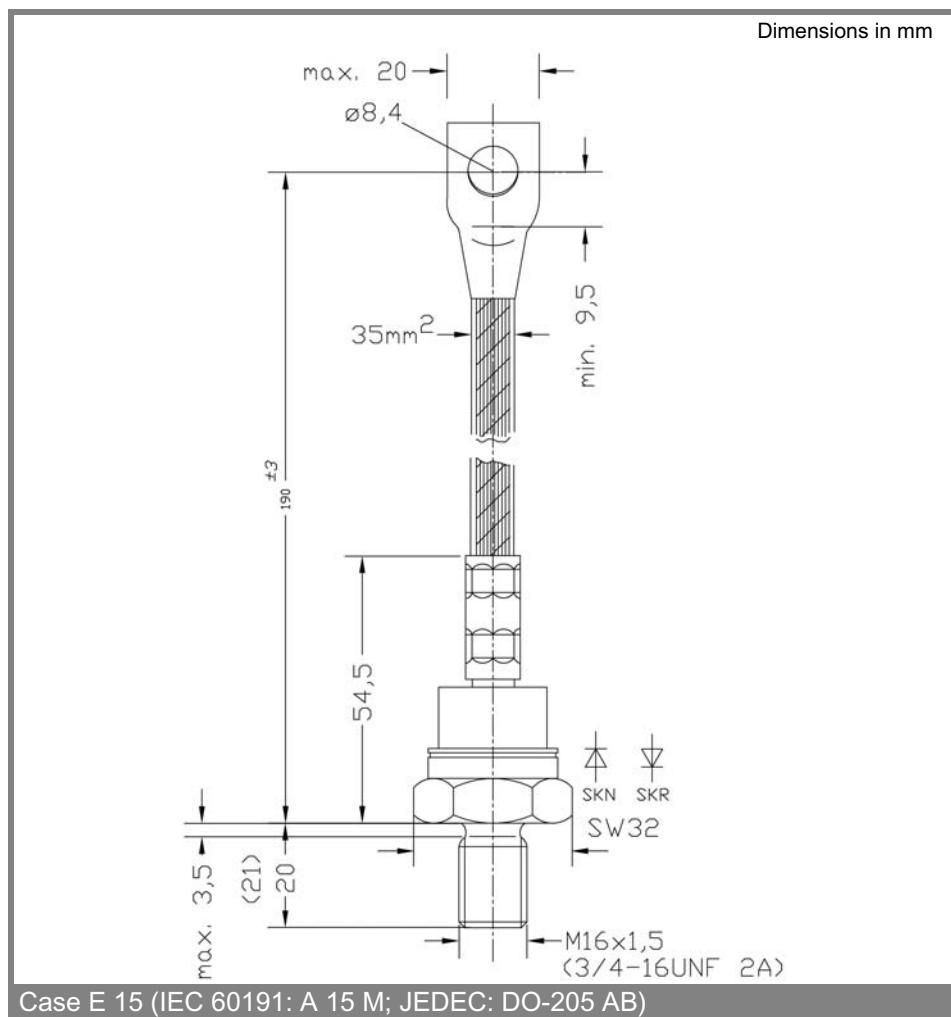


Fig. 6 Surge overload current vs. time



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